



**SPB160N04S2L-03**

**OptiMOS® Power-Transistor**

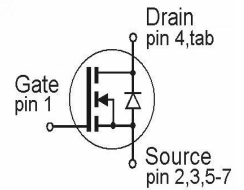
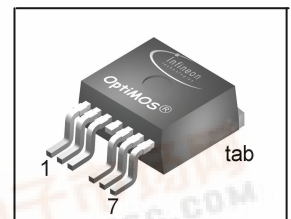
**Feature**

- N-Channel
- Enhancement mode
- Logic Level
- High Current Rating
- Low On-Resistance  $R_{DS(on)}$
- 175°C operating temperature
- Avalanche rated
- dv/dt rated

**Product Summary**

$V_{DS}$	40	V
$R_{DS(on)}$ max. SMD version	2.7	mΩ
$I_D$	160	A

P- TO263 -7-3



Type	Package	Ordering Code	Marking
SPB160N04S2L-03	P- TO263 -7-3	Q67060-S6138	P2N04L03

**Maximum Ratings**, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current <sup>1)</sup>	$I_D$	160	A
$T_C=25\text{ }^\circ\text{C}$		160	
$T_C=100\text{ }^\circ\text{C}$		160	
Pulsed drain current	$I_D$ puls	640	
$T_C=25\text{ }^\circ\text{C}$			
Avalanche energy, single pulse	$E_{AS}$	810	mJ
$I_D=80\text{ A}$ , $V_{DD}=25\text{ V}$ , $R_{GS}=25\text{ }\Omega$			
Repetitive avalanche energy, limited by $T_{jmax}^{2)}$	$E_{AR}$	30	
Reverse diode dv/dt	dv/dt	6	kV/ $\mu\text{s}$
$I_S=160\text{ A}$ , $V_{DS}=32\text{ V}$ , $dI/dt=200\text{ A}/\mu\text{s}$ , $T_{jmax}=175\text{ }^\circ\text{C}$			
Gate source voltage	$V_{GS}$	$\pm 20$	V
Power dissipation	$P_{tot}$	300	W
$T_C=25\text{ }^\circ\text{C}$			
Operating and storage temperature	$T_j, T_{stg}$	-55... +175	$^\circ\text{C}$
IEC climatic category; DIN IEC 68-1		55/175/56	



**Thermal Characteristics**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Characteristics</b>					
Thermal resistance, junction - case	$R_{thJC}$	-	-	0.5	K/W
Thermal resistance, junction - ambient, leaded	$R_{thJA}$	-	-	62	
SMD version, device on PCB: @ min. footprint @ 6 cm <sup>2</sup> cooling area <sup>3)</sup>	$R_{thJA}$	-	-	62 40	

**Electrical Characteristics, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Static Characteristics</b>					
Drain-source breakdown voltage $V_{GS}=0V, I_D=1mA$	$V_{(BR)DSS}$	40	-	-	V
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D = 250\mu A$	$V_{GS(th)}$	1.2	1.6	2	
Zero gate voltage drain current $V_{DS}=40V, V_{GS}=0V, T_j=25^\circ C$ $V_{DS}=40V, V_{GS}=0V, T_j=125^\circ C$	$I_{DSS}$	-	0.01 1	1 100	$\mu A$
Gate-source leakage current $V_{GS}=20V, V_{DS}=0V$	$I_{GSS}$	-	1	100	
Drain-source on-state resistance $V_{GS}=4.5V, I_D=80A$	$R_{DS(on)}$	-	2.7	3.7	m $\Omega$
Drain-source on-state resistance $V_{GS}=10V, I_D=80A$	$R_{DS(on)}$	-	2.1	2.7	

<sup>1</sup>Current limited by bondwire ; with an  $R_{thJC} = 0.5K/W$  the chip is able to carry  $I_D= 243A$  at  $25^\circ C$ , for detailed information see app.-note ANPS071E available at [www.infineon.com/optimos](http://www.infineon.com/optimos)

<sup>2</sup>Defined by design. Not subject to production test.

<sup>3</sup>Device on 40mm\*40mm\*1.5mm epoxy PCB FR4 with 6cm<sup>2</sup> (one layer, 70  $\mu m$  thick) copper area for drain connection. PCB is vertical without blown air.

**Electrical Characteristics**

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Dynamic Characteristics**

Transconductance	$g_{fs}$	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$ , $I_D = 160A$	115	230	-	S
Input capacitance	$C_{iss}$	$V_{GS} = 0V$ , $V_{DS} = 25V$ , $f = 1MHz$	-	6000	8000	pF
Output capacitance	$C_{oss}$		-	1900	2530	
Reverse transfer capacitance	$C_{rss}$		-	460	690	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 20V$ , $V_{GS} = 10V$ , $I_D = 160A$ , $R_G = 1.1\Omega$	-	12	18	ns
Rise time	$t_r$		-	80	120	
Turn-off delay time	$t_{d(off)}$		-	93	140	
Fall time	$t_f$		-	72	110	

**Gate Charge Characteristics**

Gate to source charge	$Q_{gs}$	$V_{DD} = 32V$ , $I_D = 160A$	-	21	28	nC
Gate to drain charge	$Q_{gd}$		-	60	90	
Gate charge total	$Q_g$	$V_{DD} = 32V$ , $I_D = 160A$ , $V_{GS} = 0$ to $10V$	-	170	230	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 32V$ , $I_D = 160A$	-	3.7	-	V

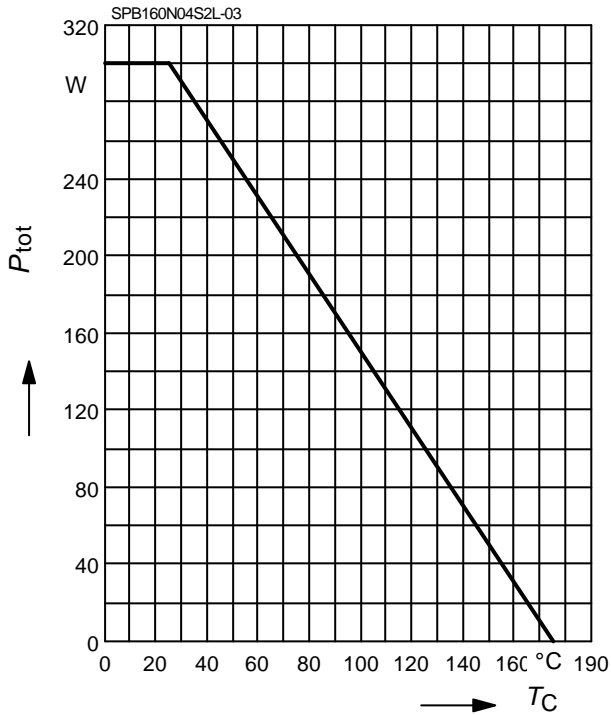
**Reverse Diode**

Inverse diode continuous forward current	$I_S$	$T_C = 25^\circ C$	-	-	160	A
Inv. diode direct current, pulsed	$I_{SM}$		-	-	640	
Inverse diode forward voltage	$V_{SD}$	$V_{GS} = 0V$ , $I_F = 80A$	-	0.9	1.3	V
Reverse recovery time	$t_{rr}$	$V_R = 20V$ , $I_F = I_S$ , $di_F/dt = 100A/\mu s$	-	62	78	ns
Reverse recovery charge	$Q_{rr}$		-	145	180	nC

### 1 Power dissipation

$$P_{tot} = f(T_C)$$

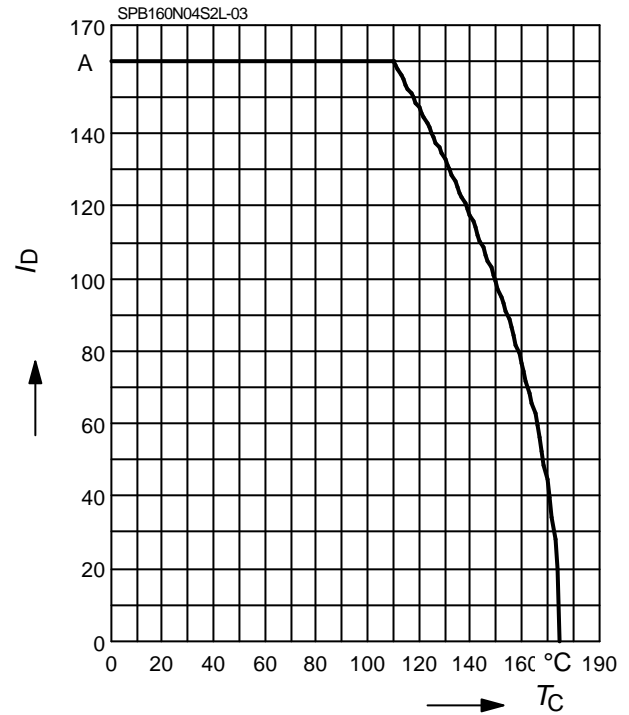
parameter:  $V_{GS} \geq 4 \text{ V}$



### 2 Drain current

$$I_D = f(T_C)$$

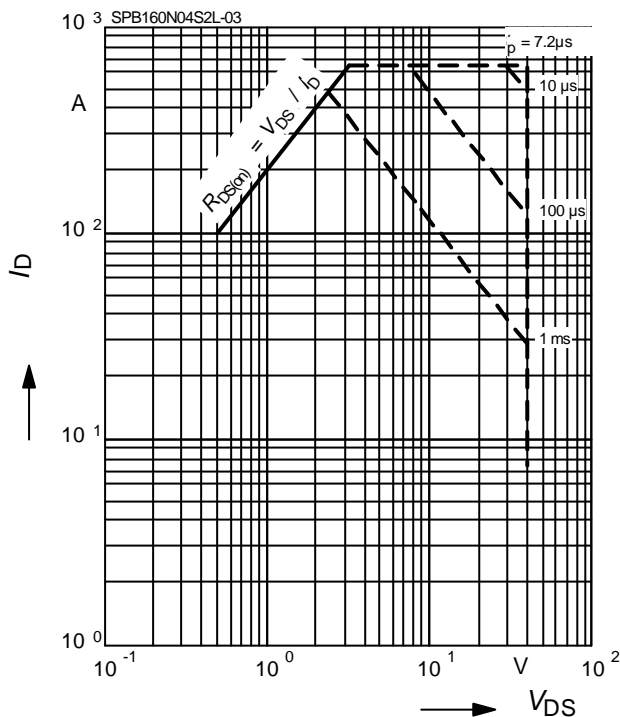
parameter:  $V_{GS} \geq 10 \text{ V}$



### 3 Safe operating area

$$I_D = f(V_{DS})$$

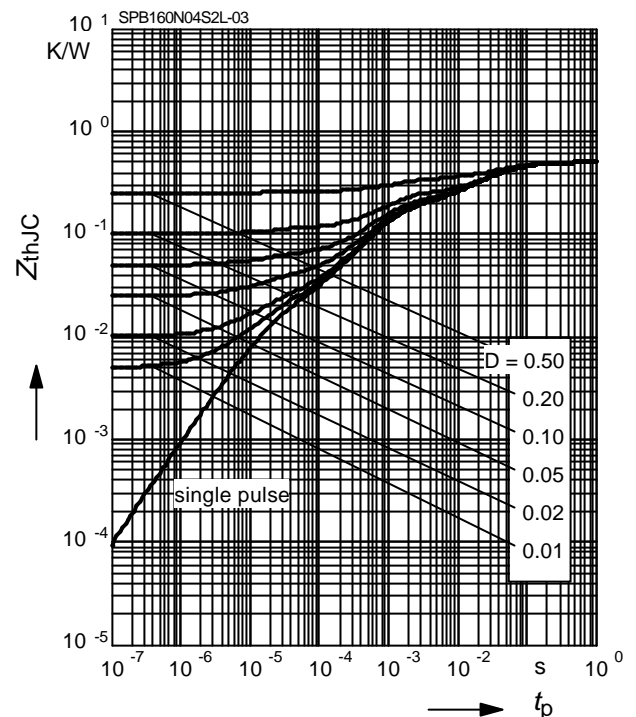
parameter:  $D = 0$ ,  $T_C = 25 \text{ °C}$



### 4 Max. transient thermal impedance

$$Z_{thJC} = f(t_p)$$

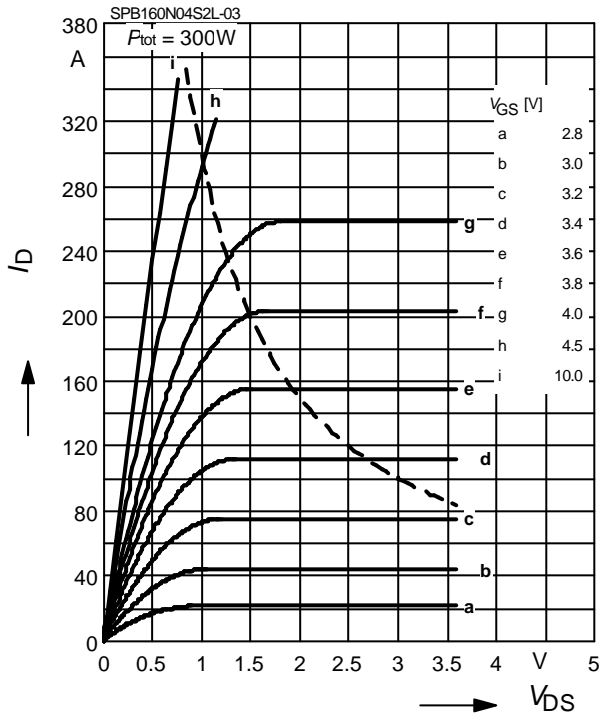
parameter:  $D = t_p/T$



**5 Typ. output characteristic**

$I_D = f(V_{DS}); T_J = 25^\circ\text{C}$

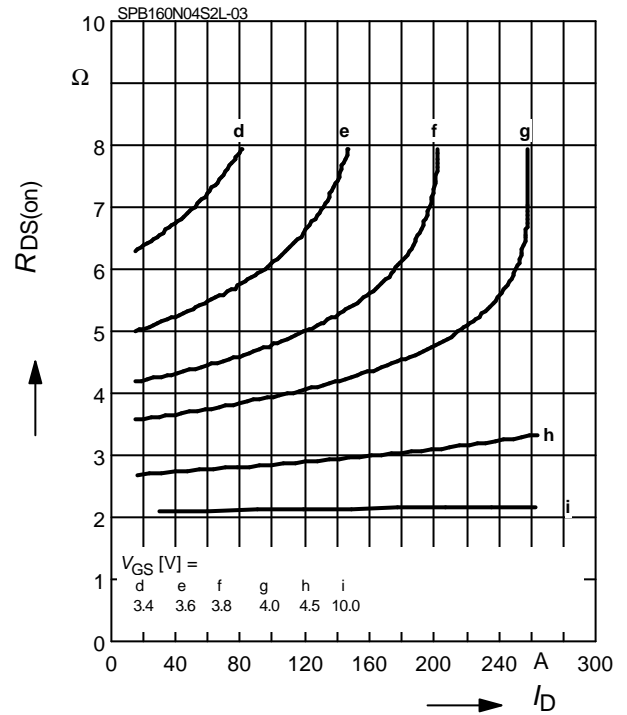
parameter:  $t_p = 80 \mu\text{s}$



**6 Typ. drain-source on resistance**

$R_{DS(on)} = f(I_D)$

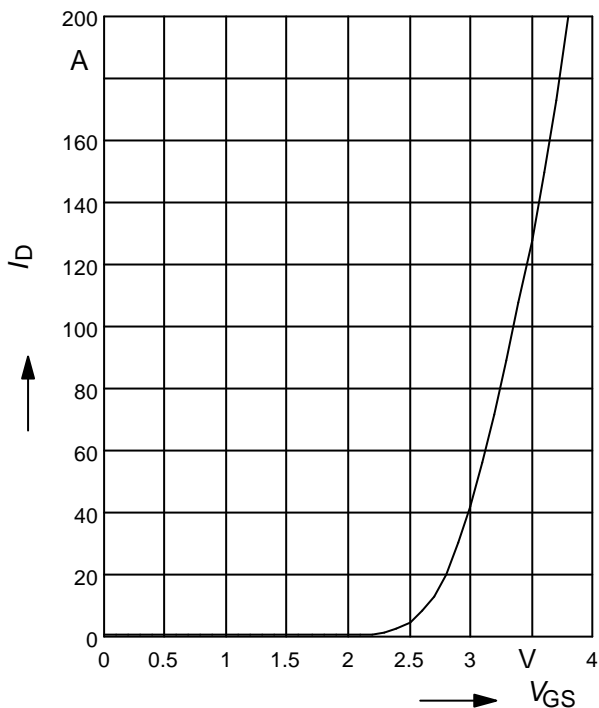
parameter:  $V_{GS}$



**7 Typ. transfer characteristics**

$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$

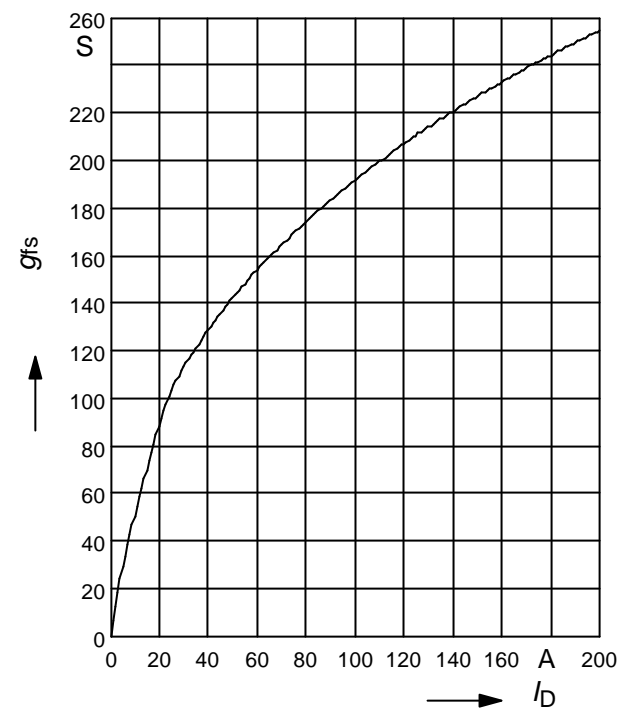
parameter:  $t_p = 80 \mu\text{s}$



**8 Typ. forward transconductance**

$g_{fs} = f(I_D); T_J = 25^\circ\text{C}$

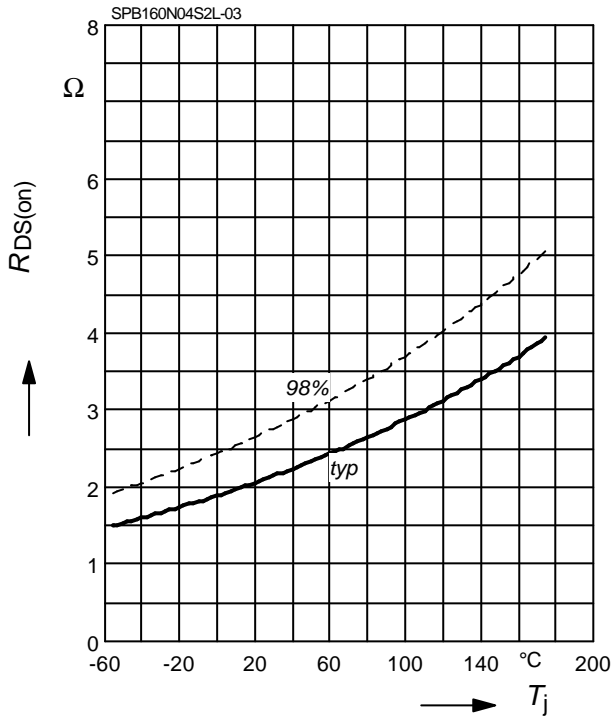
parameter:  $g_{fs}$



**9 Drain-source on-state resistance**

$R_{DS(on)} = f(T_j)$

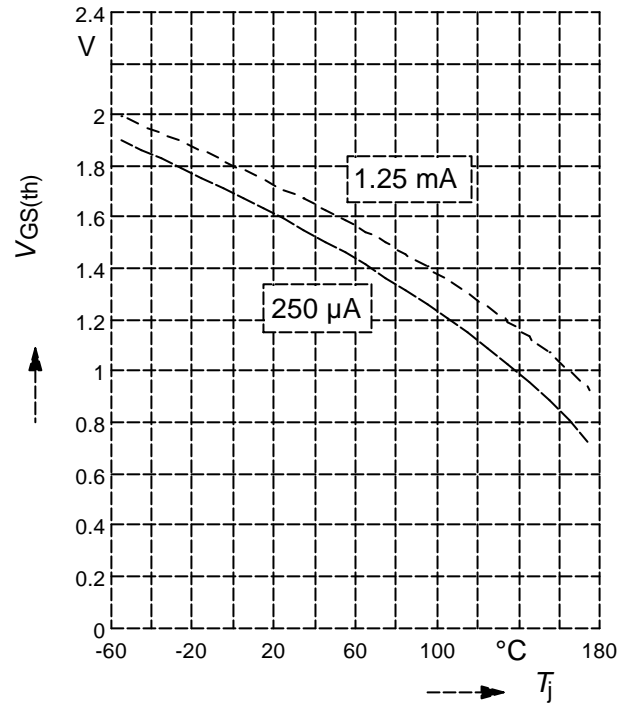
parameter:  $I_D = 80\text{ A}$ ,  $V_{GS} = 10\text{ V}$



**10 Typ. gate threshold voltage**

$V_{GS(th)} = f(T_j)$

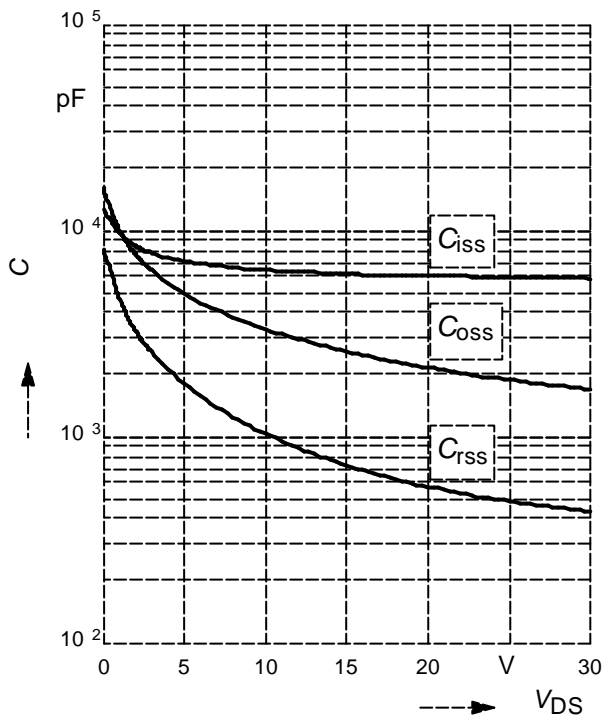
parameter:  $V_{GS} = V_{DS}$



**11 Typ. capacitances**

$C = f(V_{DS})$

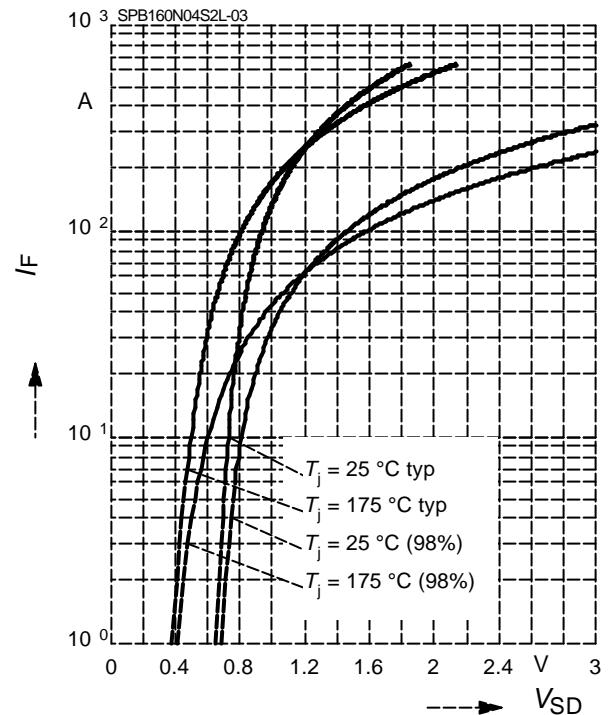
parameter:  $V_{GS} = 0\text{ V}$ ,  $f = 1\text{ MHz}$



**12 Forward character. of reverse diode**

$I_F = f(V_{SD})$

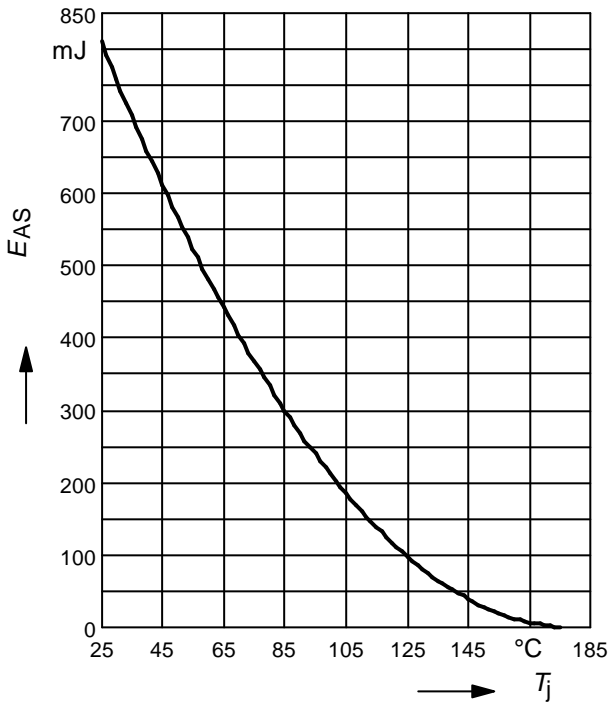
parameter:  $T_j$ ,  $t_p = 80\text{ }\mu\text{s}$



**13 Typ. avalanche energy**

$$E_{AS} = f(T_j)$$

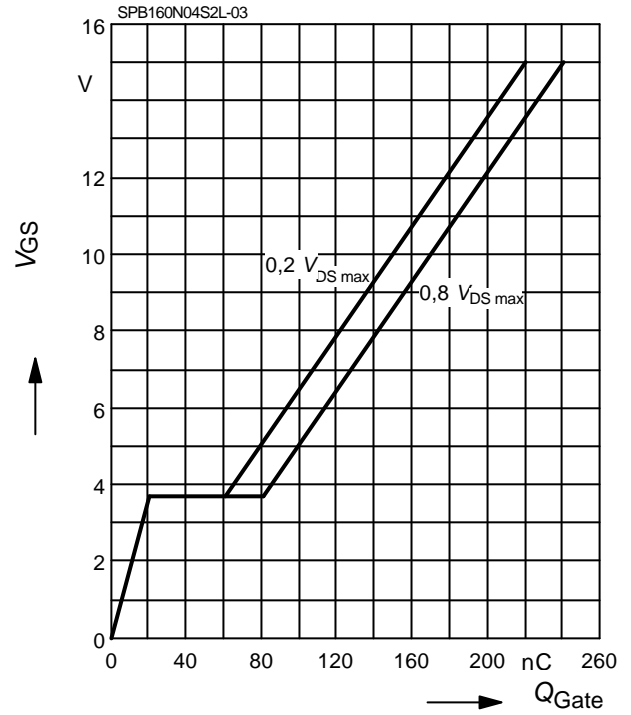
par.:  $I_D = 80 \text{ A}$ ,  $V_{DD} = 25 \text{ V}$ ,  $R_{GS} = 25 \Omega$



**14 Typ. gate charge**

$$V_{GS} = f(Q_{Gate})$$

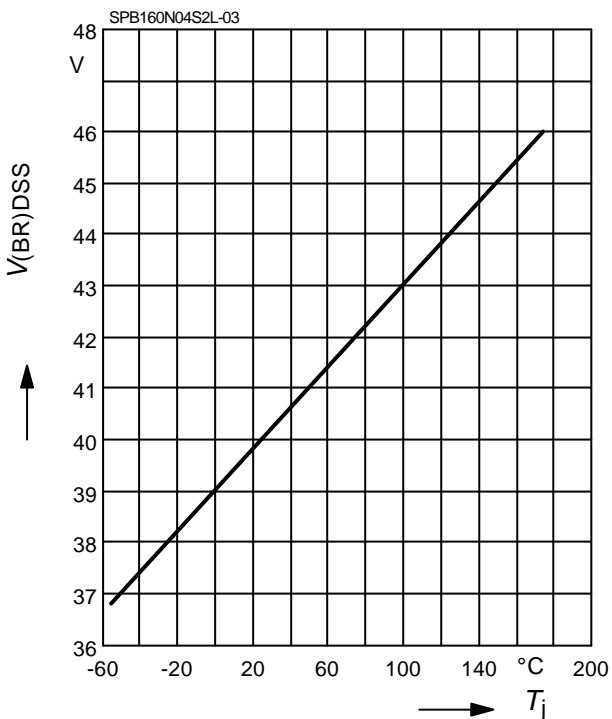
parameter:  $I_D = 160 \text{ A}$  pulsed



**15 Drain-source breakdown voltage**

$$V_{(BR)DSS} = f(T_j)$$

parameter:  $I_D = 10 \text{ mA}$





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**Further information**

Please notice that the part number is BSPB160N04S2L-03, for simplicity the device is referred to by the term SPB160N04S2L-03 throughout this documentation.